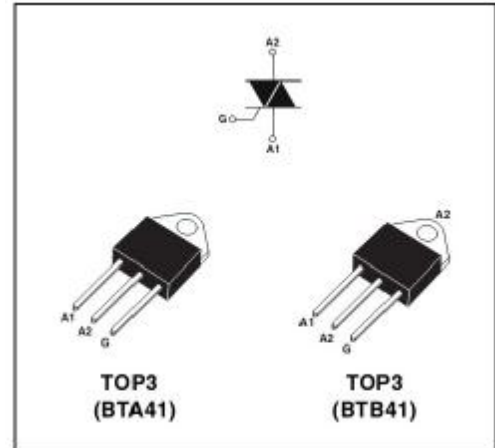


**YUhi fYg.**

- NPNPN Bi-direction Triac
- Back multilayer metal electrode
- High temperature reliability
- Glass Passivated junction chipses

**5 dd`]WU]cb.**

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**Limiting Values**

Symbol	Absolute maximum ratings parameters		Value	Unit
IT(RMS)	RMS on-state current	BTA BTB	Tc=80°C Tc=90°C	40 A
ITSM	Non repetitive surge peak on-state current		F=50HZ t=20ms	410 A
i <sup>2</sup> t	I <sup>2</sup> t value for fusing		tp=10ms	880 A <sup>2</sup> S
di/dt	Critical rate of rise of on-state current		Tj=125°C	50 A/us
VDRM/VRRM	Non repetitive surge peak off-state voltage		Tj=25°C	600 V
IGM	Peak gate current	tp=20us	Tj=125°C	8 A
PG(AV)	Average gate power dissipation		Tj=125°C	1 W
Tstg	Storage junction temperature range			-40to+150 °C
Tj	Operating junction temperature range			-40to+125 °C

• **Electrical Characteristics(4 quadrant) (T<sub>j</sub>=25°C, unless otherwise specified)**

Symbol	Test Condition	Quadrant		Value	Unit	
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =100Ω	I II III IV	MAX	I II IV	mA	
V <sub>GT</sub>				5		IV
V <sub>GD</sub>	T <sub>j</sub> =125°C		MIN	1.5		V
I <sub>H</sub>	I <sub>T</sub> =0.5A		MAX	0.2		V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I II III	MAX	80		mA
		IV		70		
dv/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>j</sub> =125°C		MIN	160		V/us
(dv/dt) <sub>c</sub>	T <sub>j</sub> =125°C		MIN	800		
				10		V/us

• **Static Characteristics**

Symbol	Test Conditions			Value	Unit
V <sub>TM</sub>	I <sub>TM</sub> = 82A	T <sub>j</sub> =25°C	MAX	1.55	V
V <sub>T0</sub>	Threshold voltage	T <sub>j</sub> =125°C	MAX	0.86	V
R <sub>d</sub>	Dynamic resistance	T <sub>j</sub> =125°C	MAX	6.4	mΩ
I <sub>DRM</sub> I <sub>RDM</sub>	V <sub>DRM</sub> = V <sub>DRM</sub>	T <sub>j</sub> =25°C	MAX	10	uA
		T <sub>j</sub> =125°C		2	mA
R <sub>th(j-c)</sub>	Junction to case (AC)	BTA		0.9	°C/W
		BTB		0.6	

**● TO-3P Dimension**
